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Understanding Embedded - DSP (Digital Signal Processors)

Embedded - DSP (Digital Signal Processors) are specialized microprocessors designed to perform complex mathematical computations on digital signals in real-time. Unlike general-purpose processors, DSPs are optimized for high-speed numeric processing tasks, making them ideal for applications that require efficient and precise manipulation of digital data. These processors are fundamental in converting and processing signals in various forms, including audio, video, and communication signals, ensuring that data is accurately interpreted and utilized in embedded systems.

Applications of Embedded - DSP (Digital Signal Processors)

Details	
Product Status	Obsolete
Type	SC140 Core
Interface	DSI, Ethernet, RS-232
Clock Rate	500MHz
Non-Volatile Memory	External
On-Chip RAM	1.436MB
Voltage - I/O	3.30V
Voltage - Core	1.20V
Operating Temperature	0°C ~ 90°C (TJ)
Mounting Type	Surface Mount
Package / Case	431-BFBGA, FCBGA
Supplier Device Package	431-FCPBGA (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/msc8126vt8000

Table 1. MSC8126 Signal Listing by Ball Designator (continued)

Des.	Signal Name	Des.	Signal Name
J3	HA26	K18	$\overline{CS2}$
J4	V_{DD}	K19	GND
J5	HA13	K20	A26
J6	GND	K21	A29
J7	PSDAMUX/PGPL5	K22	A28
J8	BADDR27	L2	HA12
J9	V_{DD}	L3	HA14
J10	CLKIN	L4	HA11
J11	BM2/TC2/BNKSEL2	L5	V_{DDH}
J12	$\overline{DBG}$	L6	V_{DDH}
J13	V_{DD}	L7	BADDR28
J14	GND	L8	$\overline{IRQ5}$/BADDR29
J15	V_{DD}	L9	GND
J16	TT3/$\overline{CS6}$	L10	GND
J17	PSDA10/PGPL0	L14	GND
J18	$\overline{BCTL1}$/$\overline{CS5}$	L15	V_{DDH}
J19	GPIO23/TDM0TDAT/$\overline{IRQ13}$	L16	GND
J20	GND	L17	GND
J21	GPIO25/TDM0RCLK/$\overline{IRQ15}$	L18	$\overline{CS3}$
J22	A30	L19	V_{DDH}
K2	HA15	L20	A27
K3	HA21	L21	A25
K4	HA16	L22	A22
K5	$\overline{PWE3}$/$\overline{PSDDQM3}$/$\overline{PBS3}$	M2	HD28
K6	$\overline{PWE1}$/$\overline{PSDDQM1}$/$\overline{PBS1}$	M3	HD31
K7	$\overline{POE}$/$\overline{PSDRAS}$/PGPL2	M4	V_{DDH}
K8	$\overline{IRQ2}$/BADDR30	M5	GND
K9	Reserved	M6	GND
K10	GND	M7	V_{DDH}
K11	GND	M8	V_{DD}
K12	GND	M9	V_{DDH}
K13	GND	M10	GND
K14	CLKOUT	M14	GND
M15	V_{DDH}	P12	V_{CCSYN}
M16	$\overline{HBRST}$	P13	GND
M17	V_{DDH}	P14	GND
M18	V_{DDH}	P15	$\overline{TA}$
M19	GND	P16	$\overline{BR}$
M20	V_{DDH}	P17	$\overline{TEA}$

Table 1. MSC8126 Signal Listing by Ball Designator (continued)

Des.	Signal Name	Des.	Signal Name
M21	A24	P18	$\overline{\text{PSDVAL}}$
M22	A21	P19	DP0/DREQ1/$\overline{\text{EXT\_BR2}}$
N2	HD26	P20	V_{DDH}
N3	HD30	P21	GND
N4	HD29	P22	A19
N5	HD24	R2	HD18
N6	$\overline{\text{PWE2}}$/$\overline{\text{PSDDQM2}}$/$\overline{\text{PBS2}}$	R3	V_{DDH}
N7	V_{DDH}	R4	GND
N8	$\overline{\text{HWBS0}}$/$\overline{\text{HDBS0}}$/$\overline{\text{HWBE0}}$/$\overline{\text{HDBE0}}$	R5	HD22
N9	$\overline{\text{HBCS}}$	R6	$\overline{\text{HWBS6}}$/$\overline{\text{HDBS6}}$/$\overline{\text{HWBE6}}$/$\overline{\text{HDBE6}}$/$\overline{\text{PWE6}}$/$\overline{\text{PSDDQM6}}$/$\overline{\text{PBS6}}$
N10	GND	R7	$\overline{\text{HWBS4}}$/$\overline{\text{HDBS4}}$/$\overline{\text{HWBE4}}$/$\overline{\text{HDBE4}}$/$\overline{\text{PWE4}}$/$\overline{\text{PSDDQM4}}$/$\overline{\text{PBS4}}$
N14	GND	R8	TSZ1
N15	$\overline{\text{HRDS}}$/HRW/$\overline{\text{HRDE}}$	R9	TSZ3
N16	$\overline{\text{BG}}$	R10	$\overline{\text{IRQ1}}$/$\overline{\text{GBL}}$
N17	$\overline{\text{HCS}}$	R11	V_{DD}
N18	$\overline{\text{CS0}}$	R12	V_{DD}
N19	$\overline{\text{PSDWE}}$/PGPL1	R13	V_{DD}
N20	GPIO26/TDM0RDAT	R14	TT0/HA7
N21	A23	R15	$\overline{\text{IRQ7}}$/DP7/DREQ4
N22	A20	R16	$\overline{\text{IRQ6}}$/DP6/DREQ3
P2	HD20	R17	$\overline{\text{IRQ3}}$/DP3/DREQ2/$\overline{\text{EXT\_BR3}}$
P3	HD27	R18	$\overline{\text{TS}}$
P4	HD25	R19	$\overline{\text{IRQ2}}$/DP2/$\overline{\text{DACK2}}$/$\overline{\text{EXT\_DBG2}}$
P5	HD23	R20	A17
P6	$\overline{\text{HWBS3}}$/$\overline{\text{HDBS3}}$/$\overline{\text{HWBE3}}$/$\overline{\text{HDBE3}}$	R21	A18
P7	$\overline{\text{HWBS2}}$/$\overline{\text{HDBS2}}$/$\overline{\text{HWBE2}}$/$\overline{\text{HDBE2}}$	R22	A16
P8	$\overline{\text{HWBS1}}$/$\overline{\text{HDBS1}}$/$\overline{\text{HWBE1}}$/$\overline{\text{HDBE1}}$	T2	HD17
P9	HCLKIN	T3	HD21
P10	GND	T4	HD1/DSISYNC
P11	GND_{SYN}	T5	HD0/SWTE
T6	$\overline{\text{HWBS7}}$/$\overline{\text{HDBS7}}$/$\overline{\text{HWBE7}}$/$\overline{\text{HDBE7}}$/$\overline{\text{PWE7}}$/$\overline{\text{PSDDQM7}}$/$\overline{\text{PBS7}}$	U21	A12
T7	$\overline{\text{HWBS5}}$/$\overline{\text{HDBS5}}$/$\overline{\text{HWBE5}}$/$\overline{\text{HDBE5}}$/$\overline{\text{PWE5}}$/$\overline{\text{PSDDQM5}}$/$\overline{\text{PBS5}}$	U22	A13
T8	TSZ0	V2	HD3/MODCK1
T9	TSZ2	V3	V_{DDH}
T10	$\overline{\text{TBST}}$	V4	GND
T11	V_{DD}	V5	D0
T12	D16	V6	D1
T13	TT1	V7	D4
T14	D21	V8	D5

Table 1. MSC8126 Signal Listing by Ball Designator (continued)

Des.	Signal Name	Des.	Signal Name
Y6	V_{DD}	AA21	A2
Y7	HD60/D60/ETHCOL/reserved	AA22	A3
Y8	HD58/D58/ETHMDC	AB2	GND
Y9	GND	AB3	HD13
Y10	V_{DDH}	AB4	HD11
Y11	HD51/D51	AB5	HD8
Y12	GND	AB6	HD62/D62
Y13	V_{DDH}	AB7	HD61/D61
Y14	HD43/D43/ETHRXD3/reserved	AB8	HD57/D57/ETHRX_ER
Y15	GND	AB9	HD56/D56/ETHRX_DV/ETHCRS_DV
Y16	V_{DDH}	AB10	HD55/D55/ETHTX_ER/reserved
Y17	GND	AB11	HD53/D53
Y18	HD37/D37/reserved	AB12	HD50/D50
Y19	HD34/D34/reserved	AB13	HD49/D49/ETHTXD3/reserved
Y20	V_{DDH}	AB14	HD48/D48/ETHTXD2/reserved
Y21	A4	AB15	HD47/D47/ETHTXD1
Y22	A5	AB16	HD45/D45
AA2	V_{DD}	AB17	HD44/D44
AA3	HD14	AB18	HD41/D41/ETHRXD1
AA4	HD12	AB19	HD39/D39/reserved
AA5	HD10	AB20	HD36/D36/reserved
AA6	HD63/D63	AB21	A1
AA7	HD59/D59/ETHMDIO	AB22	V_{DD}
AA8	GND		

2 Electrical Characteristics

This document contains detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications. For additional information, see the *MSC8126 Reference Manual*.

2.1 Maximum Ratings

CAUTION

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, normal precautions should be taken to avoid exceeding maximum voltage ratings. Reliability is enhanced if unused inputs are tied to an appropriate logic voltage level (for example, either GND or V_{DD}).

In calculating timing requirements, adding a maximum value of one specification to a minimum value of another specification does not yield a reasonable sum. A maximum specification is calculated using a worst case variation of process parameter values in one direction. The minimum specification is calculated using the worst case for the same parameters in the opposite direction. Therefore, a "maximum" value for a specification never occurs in the same device with a "minimum" value for another specification; adding a maximum to a minimum represents a condition that can never exist.

Table 2 describes the maximum electrical ratings for the MSC8126.

Table 2. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Core and PLL supply voltage	V_{DD}	–0.2 to 1.6	V
I/O supply voltage	V_{DDH}	–0.2 to 4.0	V
Input voltage	V_{IN}	–0.2 to 4.0	V
Maximum operating temperature: • 400 MHz • 500 MHz	T_J	 105 90	 °C °C
Minimum operating temperature • 400 MHz • 500 MHz	T_J	 –40 0	 °C °C
Storage temperature range	T_{STG}	–55 to +150	°C

Notes:
1. Functional operating conditions are given in **Table 3.**
2. Absolute maximum ratings are stress ratings only, and functional operation at the maximum is not guaranteed. Stress beyond the listed limits may affect device reliability or cause permanent damage.
3. **Section 3.5**, *Thermal Considerations* includes a formula for computing the chip junction temperature (T_J).

2.2 Recommended Operating Conditions

Table 3 lists recommended operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 3. Recommended Operating Conditions

Rating	Symbol	Value	Unit
Core and PLL supply voltage: • Standard — 400 MHz — 500 MHz • Reduced (300 and 400 MHz)	V_{DD} V_{CCSYN}	 1.14 to 1.26 1.16 to 1.24 1.07 to 1.13	 V V V
I/O supply voltage	V_{DDH}	3.135 to 3.465	V
Input voltage	V_{IN}	–0.2 to V_{DDH}+0.2	V
Operating temperature range: • Standard • Extended	 T_J T_J	 0 to 90 –40 to 105	 °C °C

2.3 Thermal Characteristics

Table 4 describes thermal characteristics of the MSC8126 for the FC-PBGA packages.

Table 4. Thermal Characteristics for the MSC8126

Characteristic	Symbol	FC-PBGA 20 × 20 mm[5]		Unit
		Natural Convection	200 ft/min (1 m/s) airflow	
Junction-to-ambient[1, 2]	$R_{\theta JA}$	26	21	°C/W
Junction-to-ambient, four-layer board[1, 3]	$R_{\theta JA}$	19	15	°C/W
Junction-to-board (bottom)[4]	$R_{\theta JB}$	9		°C/W
Junction-to-case[5]	$R_{\theta JC}$	0.9		°C/W
Junction-to-package-top[6]	Ψ_{JT}	1		°C/W

Notes:
1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per SEMI G38-87 and JEDEC JESD51-2 with the single layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal.
4. Thermal resistance between the die and the printed circuit board per JEDEC JESD 51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.

Section 3.5, *Thermal Considerations* provides a detailed explanation of these characteristics.

2.4 DC Electrical Characteristics

This section describes the DC electrical characteristics for the MSC8126. The measurements in **Table 5** assume the following system conditions:

- T_A = 25 °C
- V_{DD} =
  - — 400 MHz = 1.14–1.26 V_{DC}
  - — 500 MHz = 1.16–1.24 V_{DC}
- V_{DDH} = 3.3 V ± 5% V_{DC}
- GND = 0 V_{DC}

Note: The leakage current is measured for nominal V_{DDH} and V_{DD}.

Table 5. DC Electrical Characteristics

Characteristic	Symbol	Min	Typical	Max	Unit
Input high voltage[1], all inputs except CLKIN	V_{IH}	2.0	—	3.465	V
Input low voltage[1]	V_{IL}	GND	0	0.8	V
CLKIN input high voltage	V_{IHC}	2.4	3.0	3.465	V
CLKIN input low voltage	V_{ILC}	GND	0	0.8	V
Input leakage current, V_{IN} = V_{DDH}	I_{IN}	–1.0	0.09	1	µA
Tri-state (high impedance off state) leakage current, V_{IN} = V_{DDH}	I_{OZ}	–1.0	0.09	1	µA
Signal low input current, V_{IL} = 0.8 V[2]	I_L	–1.0	0.09	1	µA
Signal high input current, V_{IH} = 2.0 V[2]	I_H	–1.0	0.09	1	µA
Output high voltage, I_{OH} = –2 mA, except open drain pins	V_{OH}	2.0	3.0	—	V
Output low voltage, I_{OL}= 3.2 mA	V_{OL}	—	0	0.4	V
V_{CCSYN} PLL supply current	I_{VCCSYN}	—	2	4	mA
Internal supply current: • Wait mode • Stop mode	 I_{DDW} I_{DDS}	 — —	 375[3] 290[3]	 — —	 mA mA
Typical power 400 MHz at 1.2 V[4]	P	—	1.15	—	W

Notes:
1. See **Figure 5** for undershoot and overshoot voltages.
2. Not tested. Guaranteed by design.
3. Measured for 1.2 V core at 25°C junction temperature.
4. The typical power values were measured using an EFR code with the device running at a junction temperature of 25°C. No peripherals were enabled and the ICache was not enabled. The source code was optimized to use all the ALUs and AGUs and all four cores. It was created using CodeWarrior® 2.5. These values are provided as examples only. Power consumption is application dependent and varies widely. To assure proper board design with regard to thermal dissipation and maintaining proper operating temperatures, evaluate power consumption for your application and use the design guidelines in **Chapter 4** of this document and in *MSC8102, MSC8122, and MSC8126 Thermal Management Design Guidelines* (AN2601).

In all cases, the power-up sequence must follow the guidelines shown in **Figure 8**.

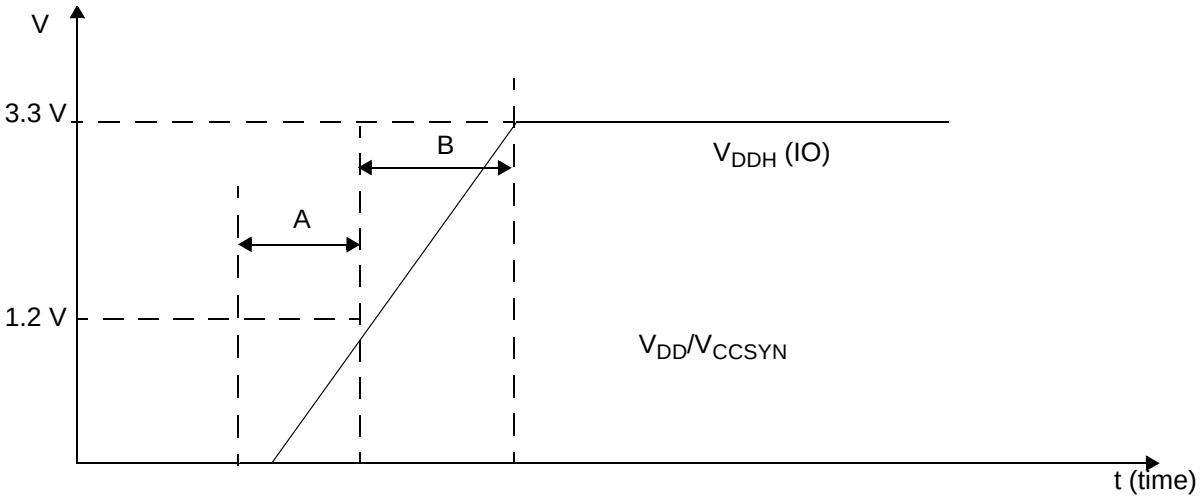


Figure 8. Power-Up Sequence for V_{DDH} and V_{DD}/V_{CCSYN}

The following rules apply:

1. During time interval A, V_{DDH} should always be equal to or less than the V_{DD}/V_{CCSYN} voltage level. The duration of interval A should be kept below 10 ms.
2. The duration of timing interval B should be kept as small as possible and less than 10 ms.

2.5.3 Clock and Timing Signals

The following sections include a description of clock signal characteristics. **Table 7** shows the maximum frequency values for internal (Core, Reference, Bus, and DSI) and external (CLKIN and CLKOUT) clocks. The user must ensure that maximum frequency values are not exceeded.

Table 7. Maximum Frequencies

Characteristic	Maximum in MHz
Core frequency	400/500
Reference frequency (REFCLK)	133/166
Internal bus frequency (BLCK)	133/166
DSI clock frequency (HCLKIN)	HCLKIN ≤ (min{100 MHz, CLKOUT})
External clock frequency (CLKIN or CLKOUT)	133/166

Table 8. Clock Frequencies

Characteristics	Symbol	400 MHz Device		500 MHz Device	
		Min	Max	Min	Max
CLKIN frequency	F_{CLKIN}	20	133.3	20	166.7
BCLK frequency	F_{BCLK}	40	133.3	40	166.7
Reference clock (REFCLK) frequency	F_{REFCLK}	40	133.3	40	166.7
Output clock (CLKOUT) frequency	F_{CLKOUT}	40	133.3	40	166.7
SC140 core clock frequency	F_{CORE}	200	400	200	500
Note: The rise and fall time of external clocks should be 5 ns maximum					

Table 15. AC Timing for SIU Outputs (continued)

No.	Characteristic	Value for Bus Speed in MHz			Units
		Ref = CLKIN		Ref = CLKOUT	
		133	166	133	
31	$\overline{\text{PSDVAL}}/\overline{\text{TEA}}/\overline{\text{TA}}$ max delay from the 50% level of the REFCLK rising edge	4.9	4.9	5.8	ns
32a	Address bus max delay from the 50% level of the REFCLK rising edge • Multi-master mode (SIUBCR[EBM] = 1) • Single-master mode (SIUBCR[EBM] = 0)	 5.5 4.2	 5.5 3.9	 6.4 5.1	 ns ns
32b	Address attributes: TT[0–1]/$\overline{\text{TBST}}$/TSZ/$\overline{\text{GBL}}$ max delay from the 50% level of the REFCLK rising edge	5.1	5.1	6.0	ns
32c	Address attributes: TT[2–4]/TC max delay from the 50% level of the REFCLK rising edge	5.7	5.7	6.6	ns
32d	BADDR max delay from the 50% level of the REFCLK rising edge	4.2	4.2	5.1	ns
33a	Data bus max delay from the 50% level of the REFCLK rising edge • Data-pipeline mode • Non-pipeline mode	 3.9 6.1	 3.7 6.1	 4.8 7.0	 ns ns
33b	DP max delay from the 50% level of the REFCLK rising edge • Data-pipeline mode • Non-pipeline mode	 5.3 6.5	 5.3 6.5	 6.2 7.4	 ns ns
34	Memory controller signals/ALE/$\overline{\text{CS}}$[0–4] max delay from the 50% level of the REFCLK rising edge	4.2	3.9	5.1	ns
35a	$\overline{\text{DBG}}/\overline{\text{BG}}/\overline{\text{BR}}/\overline{\text{DBB}}$ max delay from the 50% level of the REFCLK rising edge	4.7	4.7	5.6	ns
35b	$\overline{\text{AACK}}/\overline{\text{ABB}}/\overline{\text{TS}}/\overline{\text{CS}}$[5–7] max delay from the 50% level of the REFCLK rising edge	4.5	4.5	5.4	ns

Notes:
1. Values are measured from the 50% level of the REFCLK rising edge to the 50% signal level and assume a 20 pF load except where otherwise specified.
2. Except for specification 30, which is specified for a 10 pF load, all timings in this table are specified for a 20 pF load. Decreasing the load results in a timing decrease at the rate of 0.3 ns per 5 pF decrease in load. Increasing the load results in a timing increase at the rate of 0.15 ns per 5 pF increase in load.
3. The maximum bus frequency depends on the mode:
4. In 60x-compatible mode connected to another MSC8126 device, the frequency is determined by adding the input and output longest timing values, which results in the total delay for 20 pF output capacitance. You must also account for other influences that can affect timing, such as on-board clock skews, on-board noise delays, and so on.
   • In single-master mode, the frequency depends on the timing of the devices connected to the MSC8126.
   • To achieve maximum performance on the bus in single-master mode, disable the $\overline{\text{DBB}}$ signal by writing a 1 to the SIUMCR[BDD] bit. See the SIU chapter in the *MSC8122 Reference Manual* for details.

2.5.5.3 DMA Data Transfers

Table 17 describes the DMA signal timing.

Table 17. DMA Signals

No.	Characteristic	Ref = CLKIN		Ref = CLKOUT (1.2 V only)		Units
		Min	Max	Min	Max	
37	DREQ set-up time before the 50% level of the falling edge of REFCLK	5.0	—	5.0	—	ns
38	DREQ hold time after the 50% level of the falling edge of REFCLK	0.5	—	0.5	—	ns
39	$\overline{\text{DONE}}$ set-up time before the 50% level of the rising edge of REFCLK	5.0	—	5.0	—	ns
40	$\overline{\text{DONE}}$ hold time after the 50% level of the rising edge of REFCLK	0.5	—	0.5	—	ns
41	$\overline{\text{DACK}}$/$\overline{\text{DRACK}}$/$\overline{\text{DONE}}$ delay after the 50% level of the REFCLK rising edge	0.5	7.5	0.5	8.4	ns

The DREQ signal is synchronized with REFCLK. To achieve fast response, a synchronized peripheral should assert DREQ according to the timings in **Table 17**. **Figure 13** shows synchronous peripheral interaction.

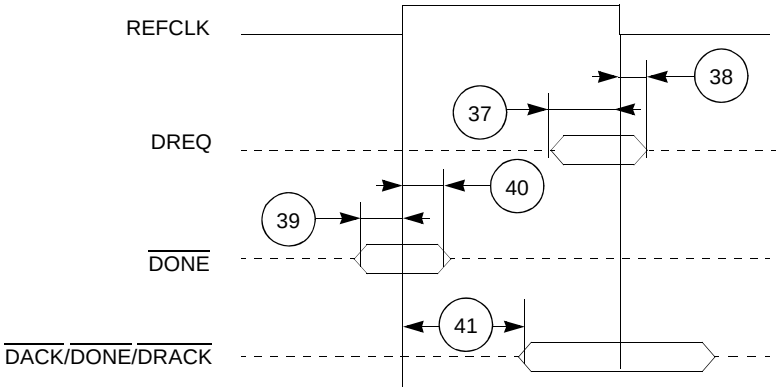


Figure 13. DMA Signals

2.5.6 DSI Timing

The timings in the following sections are based on a 20 pF capacitive load.

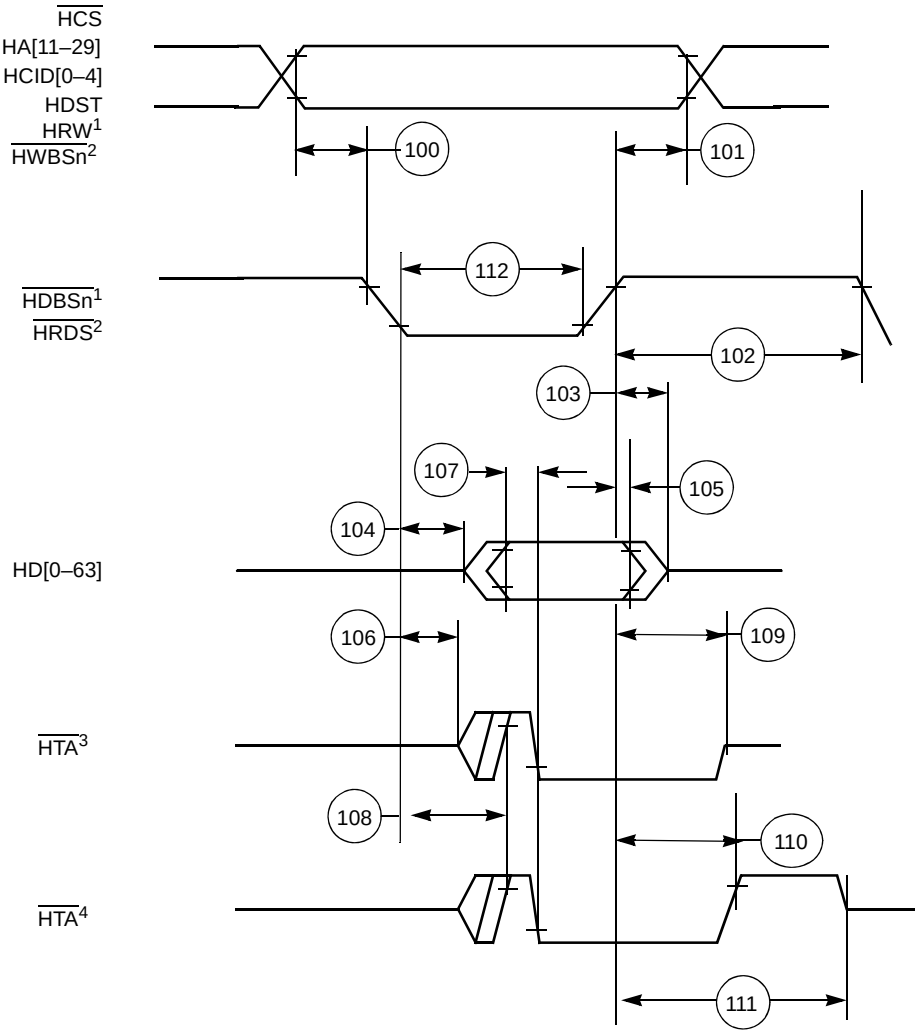
2.5.6.1 DSI Asynchronous Mode

Table 18. DSI Asynchronous Mode Timing

No.	Characteristics	Min	Max	Unit
100	Attributes[1] set-up time before strobe ($\overline{\text{HWBS[n]}}$) assertion	1.5	—	ns
101	Attributes[1] hold time after data strobe deassertion	1.3	—	ns
102	Read/Write data strobe deassertion width: • DCR[HTAAD] = 1 — Consecutive access to the same DSI — Different device with DCR[HTADT] = 01 — Different device with DCR[HTADT] = 10 — Different device with DCR[HTADT] = 11 • DCR[HTAAD] = 0	 $1.8 + T_{REFCLK}$ $5 + T_{REFCLK}$ $5 + (1.5 \times T_{REFCLK})$ $5 + (2.5 \times T_{REFCLK})$ $1.8 + T_{REFCLK}$	—	 ns ns ns ns ns
103	Read data strobe deassertion to output data high impedance	—	8.5	ns
104	Read data strobe assertion to output data active from high impedance	2.0	—	ns
105	Output data hold time after read data strobe deassertion	2.2	—	ns
106	Read/Write data strobe assertion to $\overline{\text{HTA}}$ active from high impedance	2.2	—	ns
107	Output data valid to $\overline{\text{HTA}}$ assertion	3.2	—	ns
108	Read/Write data strobe assertion to $\overline{\text{HTA}}$ valid[2] • 1.1 V core • 1.2 V core	 — —	 7.4 6.7	 ns ns
109	Read/Write data strobe deassertion to output $\overline{\text{HTA}}$ high impedance. (DCR[HTAAD] = 0, $\overline{\text{HTA}}$ at end of access released at logic 0)	—	6.5	ns
110	Read/Write data strobe deassertion to output $\overline{\text{HTA}}$ deassertion. (DCR[HTAAD] = 1, $\overline{\text{HTA}}$ at end of access released at logic 1)	—	6.5	ns
111	Read/Write data strobe deassertion to output $\overline{\text{HTA}}$ high impedance. (DCR[HTAAD] = 1, $\overline{\text{HTA}}$ at end of access released at logic 1 • DCR[HTADT] = 01 • DCR[HTADT] = 10 • DCR[HTADT] = 11	—	 $5 + T_{REFCLK}$ $5 + (1.5 \times T_{REFCLK})$ $5 + (2.5 \times T_{REFCLK})$	 ns ns ns
112	Read/Write data strobe assertion width	$1.8 + T_{REFCLK}$	—	ns
201	Host data input set-up time before write data strobe deassertion	1.0	—	ns
202	Host data input hold time after write data strobe deassertion • 1.1 V core • 1.2 V core	 1.7 1.5	 — —	 ns ns

Notes:
1. *Attributes* refers to the following signals: $\overline{\text{HCS}}$, HA[11–29], HCID[0–4], HDST, HRW, $\overline{\text{HRDS}}$, and $\overline{\text{HWBS}}$n.
2. This specification is tested in dual-strobe mode. Timing in single-strobe mode is guaranteed by design.
3. All values listed in this table are tested or guaranteed by design.

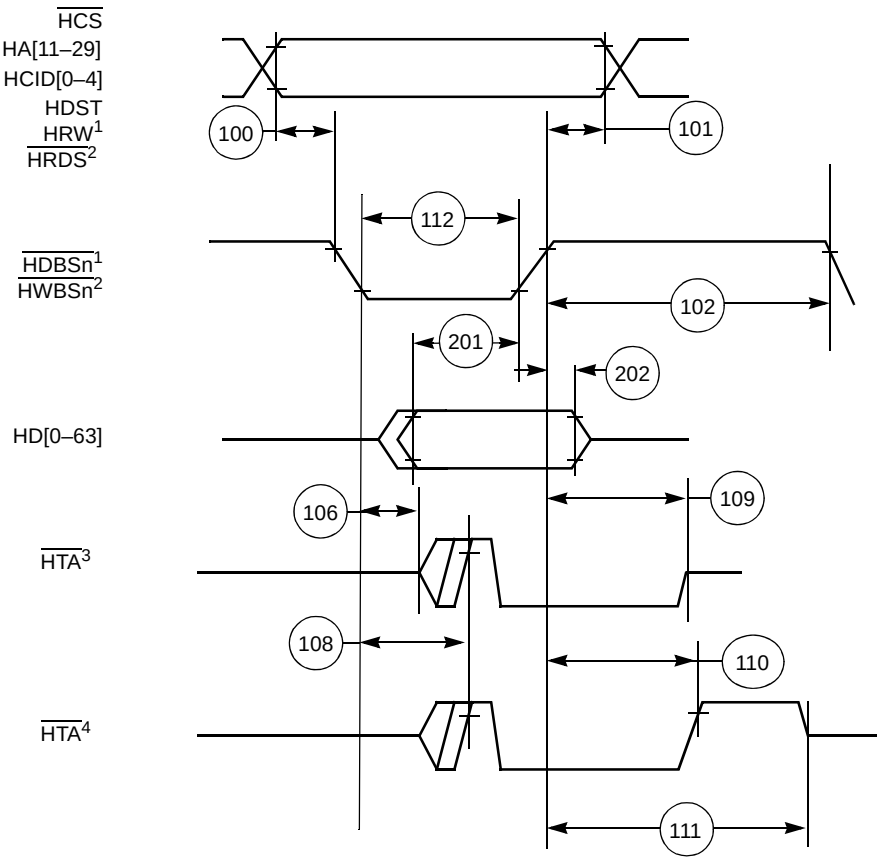
Figure 14 shows DSI asynchronous read signals timing.



Notes:
1. Used for single-strobe mode access.
2. Used for dual-strobe mode access.
3. HTA released at logic 0 (DCR[HTAAD] = 0) at end of access; used with pull-down implementation.
4. HTA released at logic 1 (DCR[HTAAD] = 1) at end of access; used with pull-up implementation.

Figure 14. Asynchronous Single- and Dual-Strobe Modes Read Timing Diagram

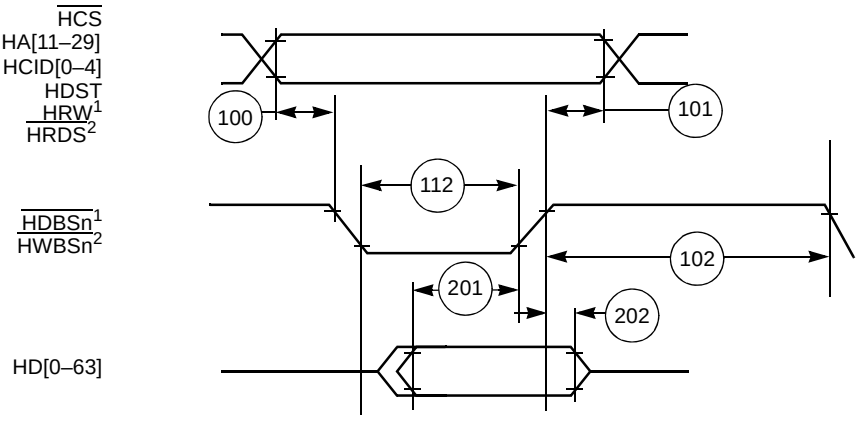
Figure 15 shows DSI asynchronous write signals timing.



Notes:
1. Used for single-strobe mode access.
2. Used for dual-strobe mode access.
3. HTA released at logic 0 (DCR[HTAAD] = 0) at end of access; used with pull-down implementation.
4. HTA released at logic 1 (DCR[HTAAD] = 1) at end of access; used with pull-up implementation.

Figure 15. Asynchronous Single- and Dual-Strobe Modes Write Timing Diagram

Figure 16 shows DSI asynchronous broadcast write signals timing.



Notes:
1. Used for single-strobe mode access.
2. Used for dual-strobe mode access.

Figure 16. Asynchronous Broadcast Write Timing Diagram

2.5.10.2 MII Mode Timing

Table 25. MII Mode Signal Timing

No.	Characteristics	Min	Max	Unit
803	ETHRX_DV, ETHRXD[0–3], ETHRX_ER to ETHRX_CLK rising edge set-up time	3.5	—	ns
804	ETHRX_CLK rising edge to ETHRX_DV, ETHRXD[0–3], ETHRX_ER hold time	3.5	—	ns
805	ETHTX_CLK to ETHTX_EN, ETHTXD[0–3], ETHTX_ER output delay • 1.1 V core • 1.2 V core	 1 1	 14.6 12.6	 ns ns

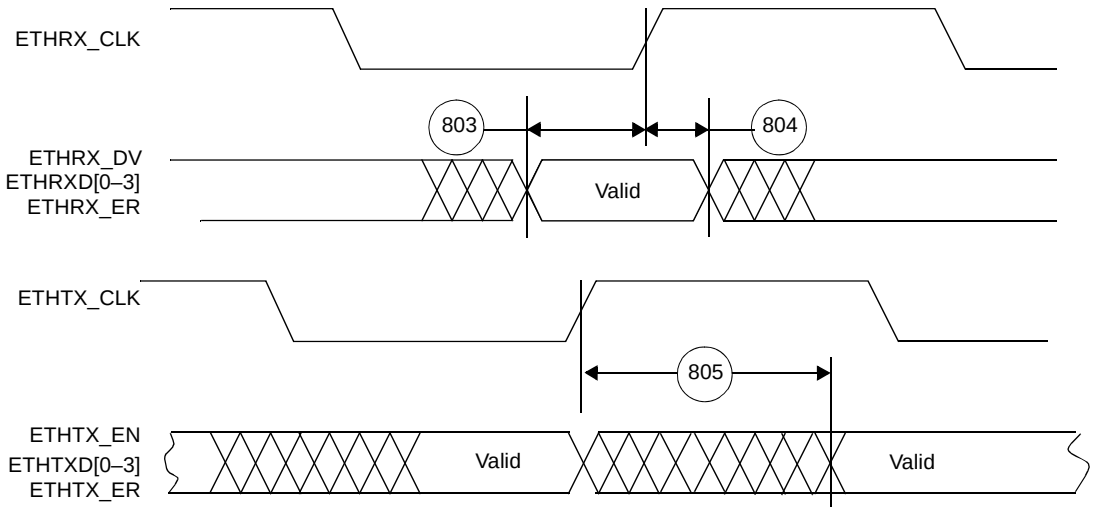


Figure 24. MII Mode Signal Timing

2.5.10.3 RMII Mode

Table 26. RMII Mode Signal Timing

No.	Characteristics	1.1 V Core		1.2 V Core		Unit
		Min	Max	Min	Max	
806	ETHTX_EN,ETHRXD[0–1], ETHCRS_DV, ETHRX_ER to ETHREF_CLK rising edge set-up time	1.6	—	2	—	ns
807	ETHREF_CLK rising edge to ETHRXD[0–1], ETHCRS_DV, ETHRX_ER hold time	1.6	—	1.6	—	ns
811	ETHREF_CLK rising edge to ETHTXD[0–1], ETHTX_EN output delay.	3	12.5	3	11	ns

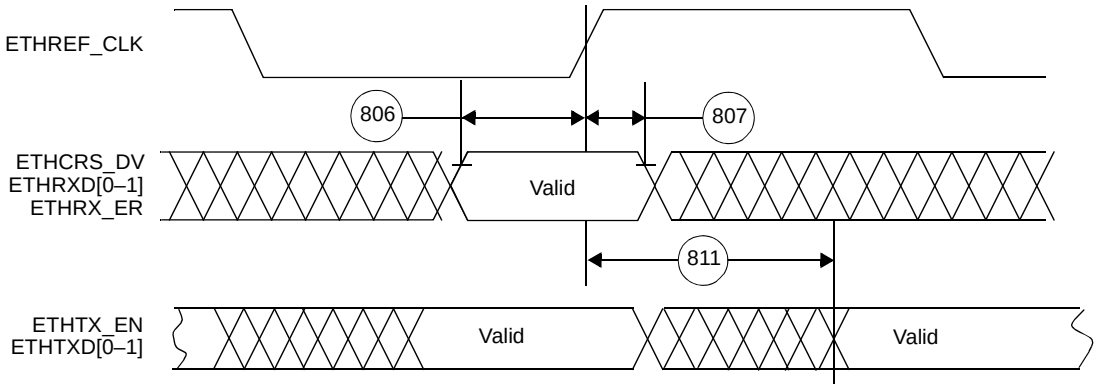


Figure 25. RMII Mode Signal Timing

3 Hardware Design Considerations

The following sections discuss areas to consider when the MSC8126 device is designed into a system.

3.1 Start-up Sequencing Recommendations

Use the following guidelines for start-up and power-down sequences:

- Assert $\overline{\text{PORESET}}$ and $\overline{\text{TRST}}$ before applying power and keep the signals driven low until the power reaches the required minimum power levels. This can be implemented via weak pull-down resistors.
- CLKIN can be held low or allowed to toggle during the beginning of the power-up sequence. However, CLKIN must start toggling before the deassertion of $\overline{\text{PORESET}}$ and after both power supplies have reached nominal voltage levels.
- If possible, bring up V_{DD}/V_{CCSYN} and V_{DDH} together. If it is not possible, raise V_{DD}/V_{CCSYN} first and then bring up V_{DDH}. V_{DDH} should not exceed V_{DD}/V_{CCSYN} until V_{DD}/V_{CCSYN} reaches its nominal voltage level. Similarly, bring both voltage levels down together. If that is not possible reverse the power-up sequence, with V_{DDH} going down first and then V_{DD}/V_{CCSYN}.

Note: This recommended power sequencing for the MSC8126 is different from the MSC8102. See **Section 2.5.2** for start-up timing specifications.

External voltage applied to any input line must not exceed the I/O supply V_{DDH} by more than 0.8 V at any time, including during power-up. Some designs require pull-up voltages applied to selected input lines during power-up for configuration purposes. This is an acceptable exception to the rule. However, each such input can draw up to 80 mA per input pin per device in the system during start-up.

During the power-up sequence, if V_{DD} rises before V_{DDH} (see **Figure 6**), current can pass from the V_{DD} supply through the device ESD protection circuits to the V_{DDH} supply. The ESD protection diode can allow this to occur when V_{DD} exceeds V_{DDH} by more than 0.8 V. Design the power supply to prevent or minimize this effect using one of the following optional methods:

- Never allow V_{DD} to exceed V_{DDH} + 0.8V.
- Design the V_{DDH} supply to prevent reverse current flow by adding a minimum 10 Ω resistor to GND to limit the current. Such a design yields an initial V_{DDH} level of V_{DD} – 0.8 V before it is enabled.

After power-up, V_{DDH} must not exceed V_{DD}/V_{CCSYN} by more than 2.6 V.

3.2 Power Supply Design Considerations

When used as a drop-in replacement in MSC8102 applications or when implementing a new design, use the guidelines described in *Migrating Designs from the MSC8102 to the MSC8122* (AN2716) and the *MSC8126 Design Checklist* (AN3374 for optimal system performance. *MSC8122 and MSC8126 Power Circuit Design Recommendations and Examples* (AN2937) provides detailed design information. See **Section 2.5.2** for start-up timing specifications.

Figure 33 shows the recommended power decoupling circuit for the core power supply. The voltage regulator and the decoupling capacitors should supply the required device current without any drop in voltage on the device pins. The voltage on the package pins should not drop below the minimum specified voltage level even for a very short spikes. This can be achieved by using the following guidelines:

- For the core supply, use a voltage regulator rated at 1.2 V with nominal rating of at least 3 A. This rating does not reflect actual average current draw, but is recommended because it resists changes imposed by transient spikes and has better voltage recovery time than supplies with lower current ratings.

  - The maximum load on CLKOUT must not exceed 10 pF.
  - Use a zero-delay buffer with a jitter less than 0.3 ns.
- All clock modes are valid in this clock scheme.

Note: See the Clock chapter in the *MSC8122 Reference Manual* for details.

- If the 60x-compatible system bus is not used and SIUMCR[PBSE] is set, $\overline{\text{PPBS}}$ can be disconnected. Otherwise, it should be pulled up.
- The following signals: SWTE, DSISYNC, DSI64, MODCK[1–2], CNFGS, CHIPID[0–3], RSTCONF and BM[0–2] are used to configure the MSC8126 and are sampled on the deassertion of the $\overline{\text{PORESET}}$ signal. Therefore, they should be tied to GND or V_{DDH} or through a pull-down or a pull-up resistor until the deassertion of the $\overline{\text{PORESET}}$ signal.
- When they are used, $\overline{\text{INT\_OUT}}$ (if SIUMCR[INTODC] is cleared), $\overline{\text{NMI\_OUT}}$, and $\overline{\text{IRQxx}}$ (if not full drive) signals must be pulled up.
- When the Ethernet controller is enabled and the SMII mode is selected, GPIO10 and GPIO14 must not be connected externally to any signal line.

Note: For details on configuration, see the *MSC8126 User's Guide* and *MSC8126 Reference Manual*. For additional information, refer to the *MSC8126 Design Checklist* (AN2903).

3.4 External SDRAM Selection

The external bus speed implemented in a system determines the speed of the SDRAM used on that bus. However, because of differences in timing characteristics among various SDRAM manufacturers, you may have use a faster speed rated SDRAM to assure efficient data transfer across the bus. For example, for 166 MHz operation, you may have to use 183 or 200 MHz SDRAM. Always perform a detailed timing analysis using the MSC8126 bus timing values and the manufacturer specifications for the SDRAM to ensure correct operation within your system design. The output delay listed in SDRAM specifications is usually given for a load of 30 pF. Scale the number to your specific board load using the typical scaling number provided by the SDRAM manufacturer.

3.5 Thermal Considerations

An estimation of the chip-junction temperature, T_J, in °C can be obtained from the following:

$$T_J = T_A + (R_{\theta JA} \times P_D) \quad \textit{Eqn. 1}$$

where

T_A = ambient temperature near the package (°C)
$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
$P_D = P_{INT} + P_{I/O}$ = power dissipation in the package (W)
$P_{INT} = I_{DD} \times V_{DD}$ = internal power dissipation (W)
$P_{I/O}$ = power dissipated from device on output pins (W)

The power dissipation values for the MSC8126 are listed in **Table 2-3**. The ambient temperature for the device is the air temperature in the immediate vicinity that would cool the device. The junction-to-ambient thermal resistances are JEDEC standard values that provide a quick and easy estimation of thermal performance. There are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. The value that more closely approximates a specific application depends on the power dissipated by other components on the printed circuit board (PCB). The value obtained using a single layer board is appropriate for tightly packed PCB configurations. The value obtained using a board with internal planes is more appropriate for boards with low power dissipation (less than 0.02 W/cm^2 with natural convection) and well separated components. Based on an estimation of junction temperature using this technique, determine whether a more detailed thermal analysis is required. Standard thermal management techniques can be used to maintain the device thermal junction temperature below its maximum. If T_J appears to be too high, either lower the ambient temperature or the power dissipation of the chip. You can verify the junction temperature by measuring the case temperature using a small diameter thermocouple (40 gauge is recommended) or an infrared temperature sensor on a spot on the device case that is painted black. The MSC8126 device case surface is too shiny (low emissivity) to yield an accurate infrared temperature measurement. Use the following equation to determine T_J:

$$T_J = T_T + (\theta_{JA} \times P_D) \quad \textit{Eqn. 2}$$

where

T_T = thermocouple (or infrared) temperature on top of the package (°C)
θ_{JA} = thermal characterization parameter (°C/W)
P_D = power dissipation in the package (W)

Note: See *MSC8102, MSC8122, and MSC8126 Thermal Management Design Guidelines* (AN2601/D).

4 Ordering Information

Consult a Freescale Semiconductor sales office or authorized distributor to determine product availability and place an order.

Part	Package Type	Spheres	Core Voltage	Operating Temperature	Core Frequency (MHz)	Order Number
MSC8126	Flip Chip Plastic Ball Grid Array (FC-PBGA)	Lead-free	1.2 V	–40° to 105°C	400	MSC8126TVT6400
		Lead-bearing				MSC8126TMP6400
		Lead-free		0° to 90°C	500	MSC8126VT8000
		Lead-bearing				MSC8126MP8000

5 Package Information

Notes:
1. All dimensions in millimeters.
2. Dimensioning and tolerancing per ASME Y14.5M–1994.
3. Features are symmetrical about the package center lines unless dimensioned otherwise.
4. Maximum solder ball diameter measured parallel to Datum A.
5. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
6. Parallelism measurement shall exclude any effect of mark on top surface of package.
7. Capacitors may not be present on all devices.
8. Caution must be taken not to short capacitors or exposed metal capacitor pads on package top.
9. FC CBGA (Ceramic) package code: 5238.
   FC PBGA (Plastic) package code: 5263.
10. Pin 1 indicator can be in the form of number 1 marking or an “L” shape marking.

Figure 35. MSC8126 Mechanical Information, 431-pin FC-PBGA Package

6 Product Documentation

- *MSC8126 Technical Data Sheet* (MSC8126). Details the signals, AC/DC characteristics, clock signal characteristics, package and pinout, and electrical design considerations of the MSC8126 device.
- *MSC8126 Reference Manual* (MSC8126RM). Includes functional descriptions of the extended cores and all the internal subsystems including configuration and programming information.
- *Application Notes*. Cover various programming topics related to the StarCore DSP core and the MSC8126 device.
- *SC140 DSP Core Reference Manual*. Covers the SC140 core architecture, control registers, clock registers, program control, and instruction set.

7 Revision History

Table 31 provides a revision history for this data sheet.

Table 31. Document Revision History

Revision	Date	Description
0	May 2004	• Initial release.
1	Jun. 2004	• Updated timing number 32b. • Updated DSI timing specifications.
2	Sep 2004	• New orderable parts added with other core voltage and temperature options. • Updated thermal characteristics. • In Table 2-14, removed references to 30 pF. • Design guidelines and layout recommendations updated.
3	Nov. 2004	• Added 500 MHz core and 166 MHz bus speed options. • Definitions of GPIO[27–28] updated. • Bus, TDM, and GPIO timing updated. I^2C timing changed to GPIO timing. • GPIO[27–28] connections updated. MWBEn replaced with correct name HWBEn. • Design guidelines update.
4	Jan. 2005	• Package type changed to FC-PBGA for all frequencies. • Low-voltage 300 MHz power changed to 1.1 V. • $\overline{\text{HRESET}}$ and $\overline{\text{SRESET}}$ definitions updated. • Undershoot and overshoot values added for V_{DDH}. • RMII timing updated. • Design guidelines updated and reorganized.
5	May 2005	• Multiple AC timing specifications updated.
6	May 2005	• Multiple AC timing specifications updated.
7	Jul. 2005	• Multiple AC timing specifications updated.
8	Jul. 2005	• AC specification table layout modified.
9	Sep. 2005	• ETHTX_EN type and $\overline{\text{TRST}}$ description updated. • Package drawing updated. • Clock specifications updated. • Start-up sequence updated.
10	Oct 2005	• V_{DDH} + 10% changed to V_{DDH} + 8% in **Figure 2-1**. • V_{DDH} +20% changed to V_{DDH} + 17% in **Figure 2-1**.
11	Apr 2006	• Reset timing updated to reflect actual values in **Table 2-11**.
12	Oct. 2006	• Added new timings 17 and 18 for IRQ set time and pulse width in **Table 2-13**
13	Dec. 2007	• Converted to new data sheet format. • Added PLL supply current to **Table 5** in **Section 2.4**. • Modified **Figure 5** in **Section 2.4** to make it clear that the time limits for undershoot referred to values below –0.3 V and not GND. • Added cross-references between **Sections 2.5.2** and **Section 3.1** and **3.2**. • Added power-sequence guidelines to **Sections 2.5.2**. • Added CLKIN jitter characteristic specifications to Table 9. • Added additional guidelines to prevent reverse current to **Section 3.1**. • Added connectivity guidelines for DSI in sliding windows mode to **Section 3.3**.
14	May 2008	• Changed V_{IL} maximum and reference value to 0.8 V in **Table 5**.
15	Dec 2008	• Clarified the wording of note 2 in **Table 15** on p. 24.

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Japan
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Asia/Pacific:
Freescale Semiconductor China Ltd.
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LDCForFreescaleSemiconductor
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